

TLE4968-1K

High Precision Automotive Hall Effect Latch

Technical Product Description

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Revision History

Page or Item	Subjects (major changes since previous revision)
Rev. 1.0, 2012-01-17	

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Table of Contents

	Table of Contents	4
1	Product Description	5
1.1	Overview	5
1.2	Features	5
1.3	Target Applications	5
2	Functional Description	6
2.1	General	6
2.2	Pin Configuration (top view)	6
2.3	Pin Description	6
2.4	Block Diagram	7
2.5	Functional Block Description	7
3	Specification	9
3.1	Application Circuit	9
3.2	Absolute Maximum Ratings	11
3.3	Operating Range	12
3.4	Electrical and Magnetic Characteristics	12
4	Package Information	14
4.1	Package Outline PG-SC59-3-5	14
4.2	Footprint	14
4.3	PG-SC59-3-5 Distance between Chip and Package	15
4.4	Package Marking	15

1 Product Description



1.1 Overview

The TLE4968-1 is a high precision Hall effect bipolar switch with highly accurate switching thresholds for operating temperatures up to 170°C.



Figure 1-1 Image of TLE4968-1 in the PG-SC59-3-5 package

1.2 Features

- 3.0V to 32 V operating supply voltage
- Operation from unregulated power supply
- Reverse polarity protection (-18V)
- Overvoltage capability up to 42 V without external resistor
- Output overcurrent & overtemperature protection
- Active error compensation
- High stability of magnetic thresholds
- Low jitter (typ. 0.35µs)
- High ESD performance
- SOT23 like SMD package PG-SC59-3-5

1.3 Target Applications

Target applications for the TLE496x Hall switch family are all applications which require a high precision Hall switch with a operating temperature range from -40°C to 170°C. Its superior supply voltage range from 3.0 V to 32V with overvoltage capability (e.g. load-dump) up to 42 V without external resistor makes it ideally suited for automotive and industrial applications.

The TLE4968-1 has very low magnetic thresholds and a bipolar switching behavior. It is therefore especially suited for applications which require a high sensitivity device and an output switching close to zero magnetic field values. Possible applications are BLDC rotor position measurement or speed and position measurements in camshaft or transmission applications.

Table 1-1 Ordering Information

Product Name	Product Type	Ordering Code	Package
TLE4968-1K	Bipolar Hall Latch	SP000847992	PG-SC59-3-5

2 Functional Description

2.1 General

The TLE4968-1 is an integrated Hall effect switch designed specifically for highly accurate applications with superior supply voltage capability, operating temperature range and temperature stability of the magnetic thresholds.

2.2 Pin Configuration (top view)

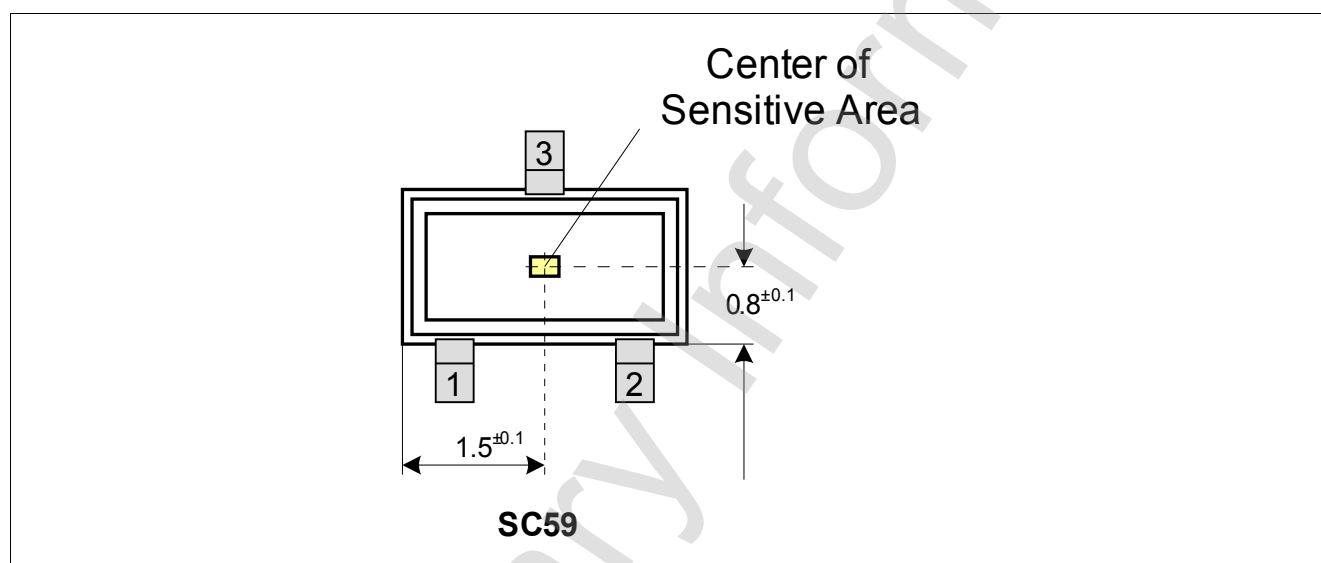


Figure 2-1 Pin Configuration and Center of Sensitive Area

2.3 Pin Description

Table 2-1 Pin Description PG-SC59-3-5

Pin No.	Symbol	Function
1	VDD	Supply voltage
2	Q	Output
3	GND	Ground

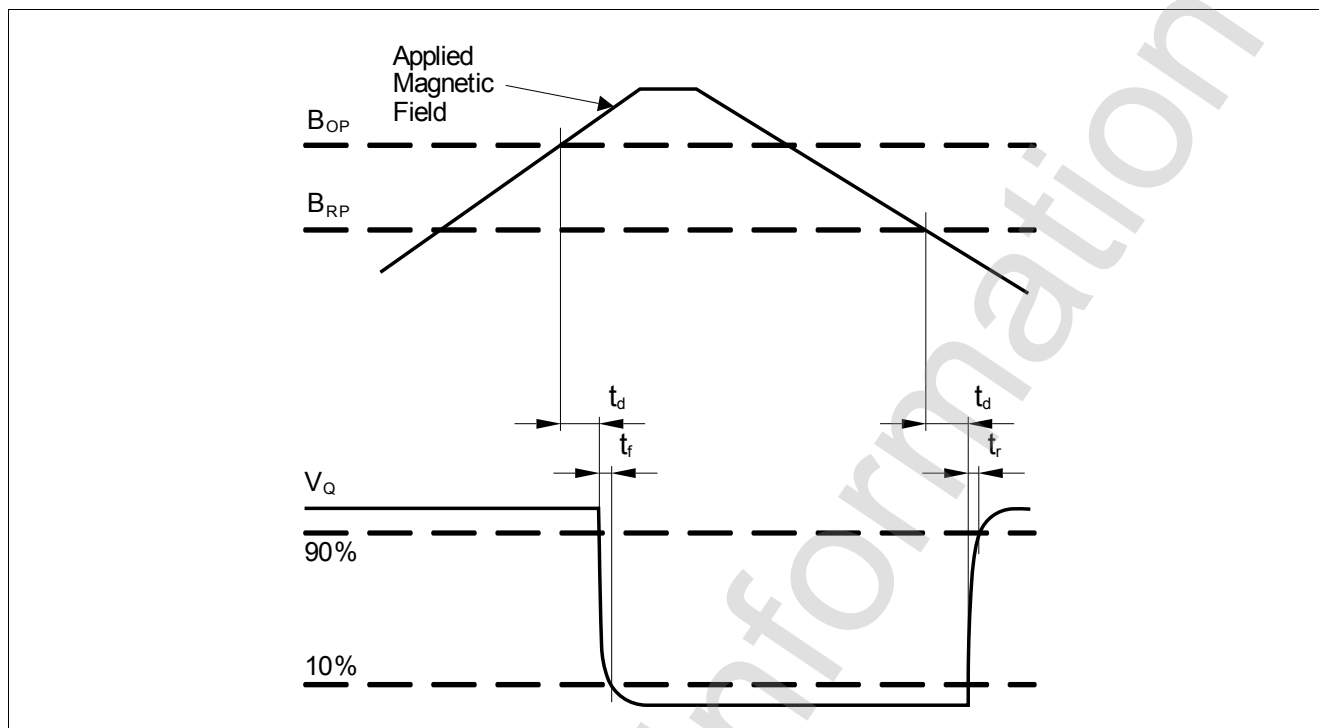


Figure 2-3 Timing Diagram TLE4968-1

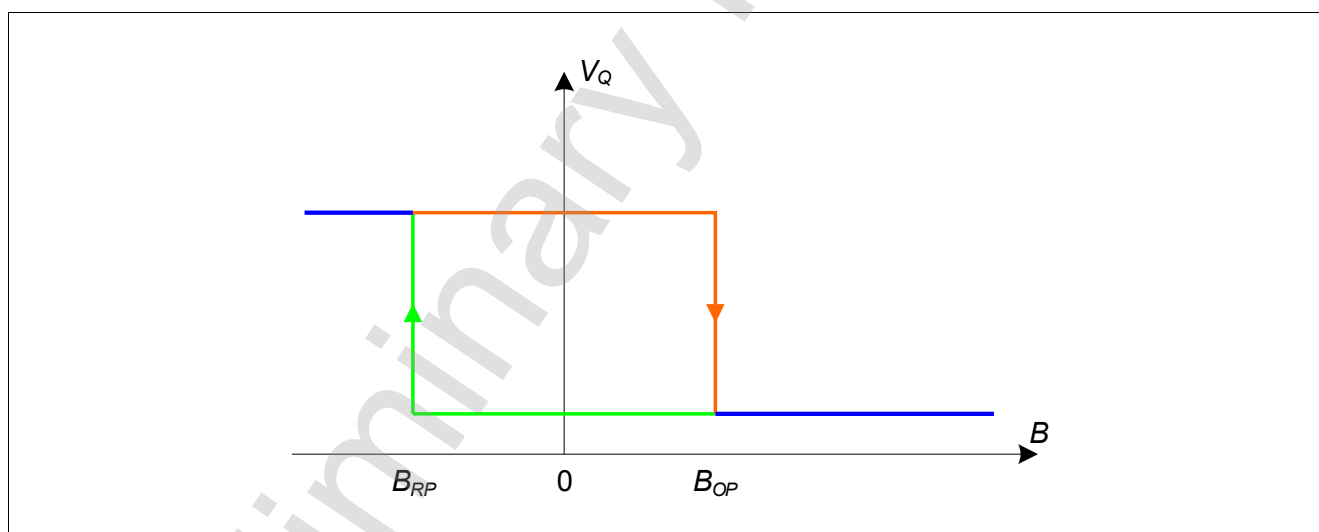


Figure 2-4 Output Signal TLE4968-1

3 Specification

3.1 Application Circuit

The following **Figure 3-1** shows one option of an application circuit. As explained above the resistor R_S can be left out (see **Figure 3-2**). The resistor R_Q has to be in a dimension to match the applied V_S to keep I_Q limited to the operating range of maximal 25mA.

e.g.:

$$V_S = 12\text{ V}$$

$$I_Q = 12\text{ V}/1200\Omega = 10\text{ mA}$$

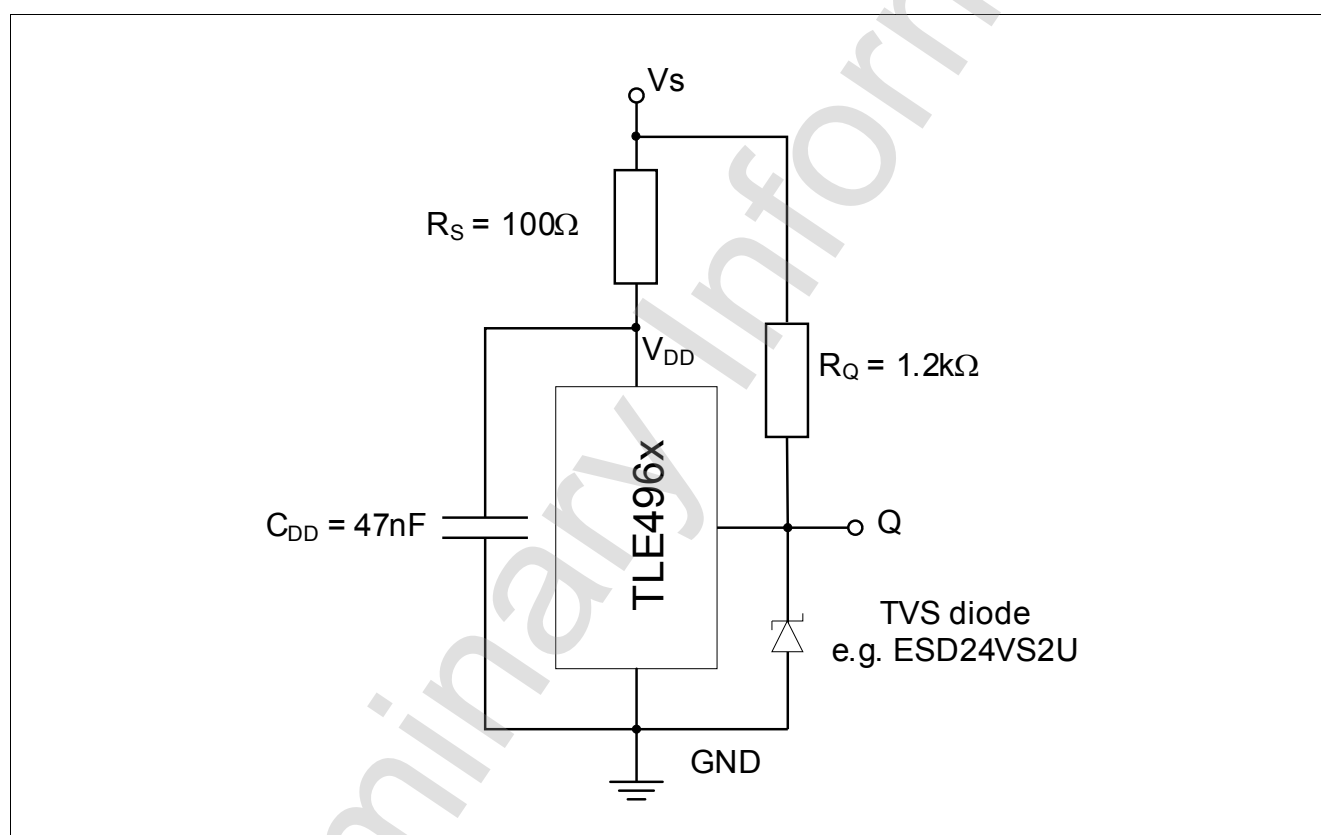


Figure 3-1 Application Circuit 1: with external resistor

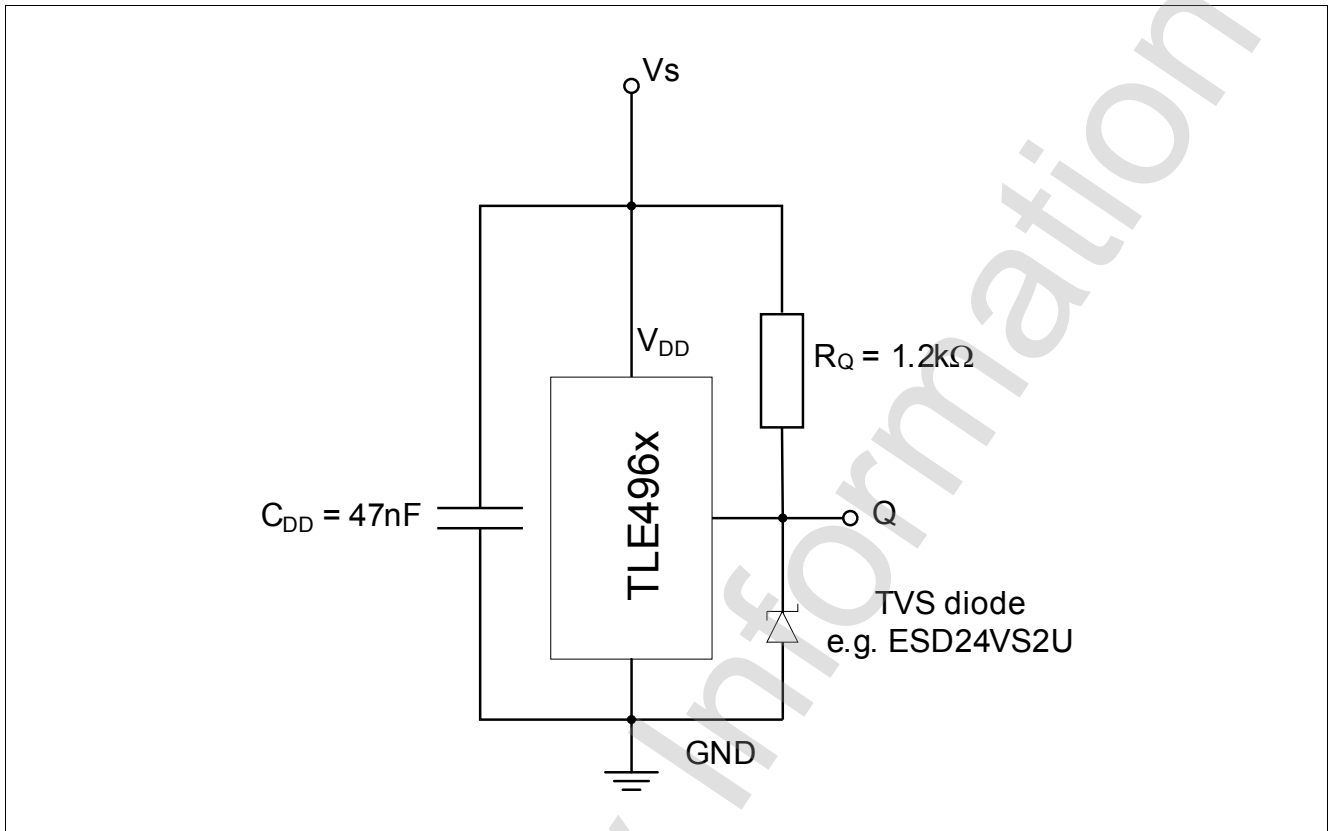


Figure 3-2 Application Circuit 2: without external resistor

3.2 Absolute Maximum Ratings

Table 3-1 Absolute Maximum Rating Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	V_{DD}	-18		32 42	V	10h, no external resistor required
Output voltage	V_Q	0		32	V	
Reverse output current	I_Q	-70			mA	
Junction temperature	T_J	-40		155 165 175 195	°C	for 2000h (not additive) for 1000h (not additive) for 168h (not additive) for 3 x 1h (additive)
Thermal resistance Junction ambient	R_{thJA}			300	K/W	for PG-SC59-3-5
Thermal resistance Junction lead	R_{thJL}			100	K/W	for PG-SC59-3-5

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

Calculation of the dissipated power P_{DIS} and junction temperature T_J of the chip (SC59 example):

e.g for: $V_{DD} = 12\text{ V}$, $I_S = 2.5\text{ mA}$, $V_{QSAT} = 0.5\text{ V}$, $I_Q = 20\text{ mA}$

Power dissipation: $P_{DIS} = 12\text{ V} \times 2.5\text{ mA} + 0.5\text{ V} \times 20\text{ mA} = 30\text{ mW} + 10\text{ mW} = 40\text{ mW}$

Temperature $\Delta T = R_{thJA} \times P_{DIS} = 300\text{ K/W} \times 40\text{ mW} = 12\text{ K}$

For $T_A = 150^\circ\text{C}$: $T_J = T_A + \Delta T = 150^\circ\text{C} + 12\text{ K} = 162^\circ\text{C}$

Table 3-2 ESD Protection¹⁾ ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
ESD voltage (HBM) ²⁾	V_{ESD}	-7		7	kV	$R = 1.5\text{ k}\Omega$, $C = 100\text{ pF}$
ESD voltage (SDM) ³⁾		-1		1		
ESD voltage (system level) ⁴⁾		-15		15		with circuit shown in Figure 3-1 & Figure 3-2

1) Characterization of ESD is carried out on a sample basis.

2) Human Body Model (HBM) tests according to EIA/JESD22-A114

3) Socket device model (SDM) tests according to EOS/ESD-DS5.3-1993

4) Gun test (2k Ω / 330pF or 330 Ω / 150pF) according to ISO 10605-2008

3.3 Operating Range

The following operating conditions must not be exceeded in order to ensure correct operation of the TLE4968-1K. All parameters specified in the following sections refer to these operating conditions unless otherwise mentioned.

Table 3-3 Operating Conditions Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	V_{DD}	3.0		32 ¹⁾	V	
Output voltage	V_Q	0		32	V	
Junction temperature	T_j	-40		170	°C	
Output current	I_Q	0		25	mA	
Magnetic signal input frequency ²⁾	f_{SW}	0		10	kHz	

1) Latch-up test with factor 1.5 is not covered. Please see max ratings also.

2) For operation at the maximum switching frequency the magnetic input signal must be 1.4 times higher than for static fields. This is due to the -3dB corner frequency of the internal low-pass filter in the signal path.

3.4 Electrical and Magnetic Characteristics

Product characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production and correspond to $V_{DD} = 12\text{ V}$ and $T_A = 25^\circ\text{C}$. The below listed specification is valid in combination with the application circuit shown in [Figure 3-1](#) and [Figure 3-2](#)

Table 3-4 General Electrical Characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply current	I_S	1.1	1.6	2.5	mA	
Reverse current	I_{SR}		0.05	1	mA	for $V_{DD} = -18\text{V}$
Output saturation voltage	V_{QSAT}		0.2	0.5	V	$I_Q = 20\text{mA}$
			0.24	0.6	V	$I_Q = 25\text{mA}$
Output leakage current	I_{QLEAK}			10	μA	
Output current limitation	I_{QLIMIT}	30	56	70	mA	internally limited & thermal shutdown
Output fall time ¹⁾	t_f	0.17	0.4	1	μs	1.2k Ω / 50pF, see Figure 2-3
Output rise time ¹⁾	t_r	0.4	0.5	1	μs	1.2k Ω / 50pF, see Figure 2-3
Output jitter ¹⁾²⁾	t_{QJ}		0.35	1	μs	For square wave signal with 1kHz
Delay time ¹⁾³⁾	t_d	12	15	30	μs	see Figure 2-3
Power-on time ¹⁾⁴⁾	t_{PON}		80	150	μs	$V_{DD} = 3\text{ V}$, $B \leq B_{RP} - 0.5\text{ mT}$ or $B \geq B_{OP} + 0.5\text{ mT}$
Chopper frequency ¹⁾	f_{OSC}		350		kHz	

1) Not subject to production test, verified by design/characterization

2) Output jitter is the 1σ value of the output switching distribution

3) Systematic delay between magnetic threshold reached and output switching

4) Time from applying $V_{DD} = 3.0\text{ V}$ to the sensor until the output is valid

Table 3-5 Magnetic Characteristics

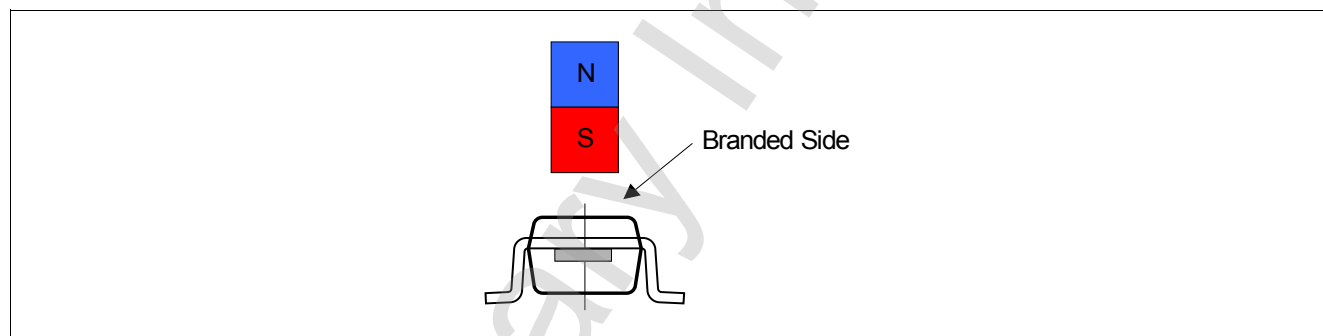
Parameter	Symbol	T (°C)	Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Operating point	B _{OP}	-40...170	-0.2	1.0	2.25	mT	
Release point	B _{RP}	-40...170	-2.25	-1.0	0.2	mT	
Hysteresis	B _{HYS}	-40...170	1.5	2.0	2.5	mT	
Effective noise value of the magnetic switching points ¹⁾	B _{Neff}	25		62		μT	
Temperature compensation of magnetic thresholds ²⁾	T _C			0		ppm/K	

1) The magnetic noise is normal distributed and can be assumed as nearly independent to frequency without sampling noise or digital noise effects. The typical value represents a the rms-value and corresponds therefore to a 1 σ probability of normal distribution. Consequently a 3 σ value corresponds to 99.7% probability of appearance.

2) Not subject to production test, verified by design/characterization

Field Direction Definition

Positive magnetic fields are defined with the south pole of the magnet to the branded side of package.


Figure 3-3 Definition of magnetic field direction PG-SC59-3-5

4 Package Information

The TLE4968-1 is available in the SMD package PG-SC59-3-5 with a SOT23 like pinout and footprint.

4.1 Package Outline PG-SC59-3-5

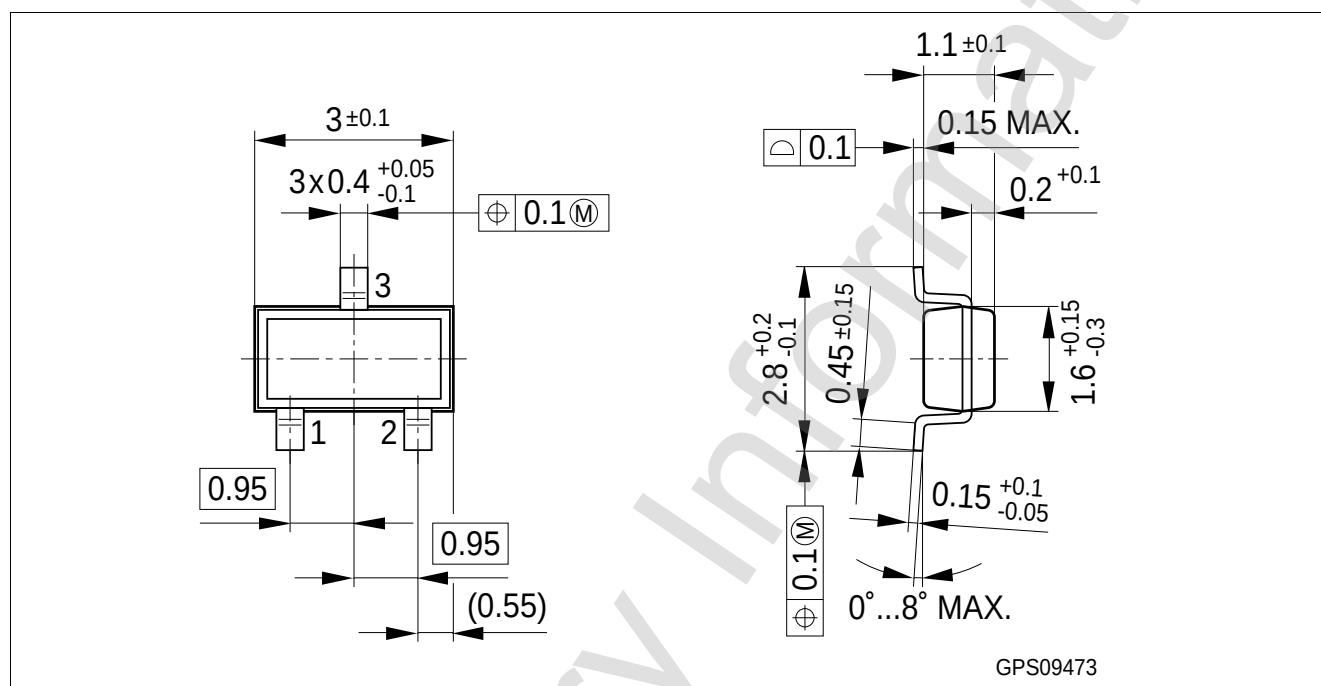


Figure 4-1 PG-SC59-3-5 Package Outline (All dimensions in mm)

4.2 Footprint

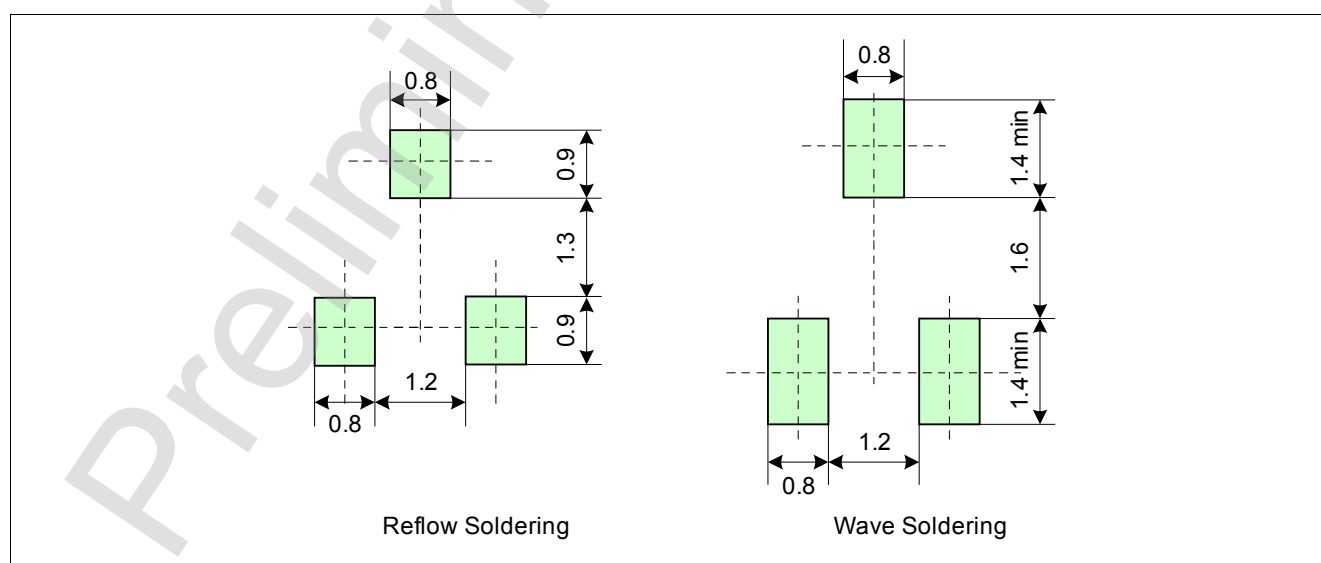


Figure 4-2 Footprint PG-SC59-3-5 and PG-SOT23

4.3 PG-SC59-3-5 Distance between Chip and Package

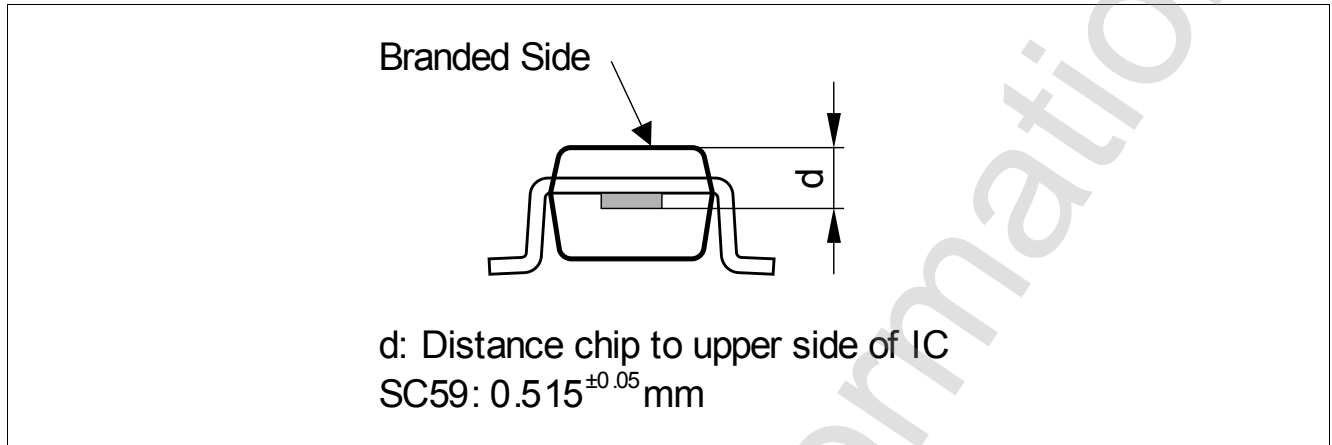


Figure 4-3 Distance between chip and package

4.4 Package Marking

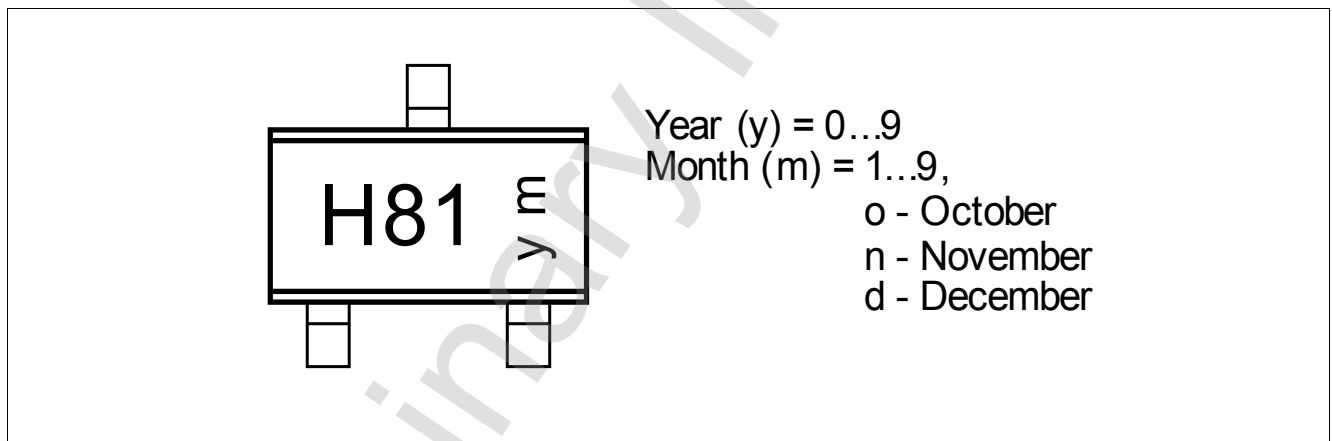


Figure 4-4 Marking of TLE4968-1K

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